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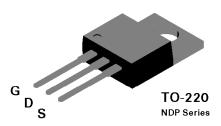
NDP6060 / NDB6060 N-Channel Enhancement Mode Field Effect Transistor

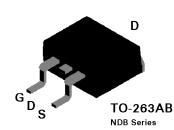
General Description

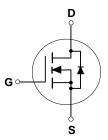
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

- 48A, 60V. $R_{DS(ON)} = 0.025\Omega$ @ $V_{GS} = 10V$.
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R_{DS(ON)}.
- TO-220 and TO-263 (D²PAK) package for both through hole and surface mount applications.







Absolute Maximum Ratings

 $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	NDP6060	NDB6060	Units
V _{DSS}	Drain-Source Voltage	60		
V_{DGR}	Drain-Gate Voltage ($R_{GS} \le 1 \text{ M}\Omega$)	(V	
V _{GSS}	Gate-Source Voltage - Continuous	±	V	
	- Nonrepetitive (t _p < 50 µs)	±		
I _D	Drain Current - Continuous T _c =25°C		48	А
	- Continuous T _c =100°C	;	32	
	- Pulsed	1	144	
P _D	Total Power Dissipation @ T _C = 25°C	1	100	W
	Derate above 25°C	0	W/°C	
T _J ,T _{STG}	Operating and Storage Temperature Range	-65	to 175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	2	275	°C

Symbol	Parameter	Conditions			Тур	Max	Units
DRAIN-SC	DURCE AVALANCHE RATINGS (Note 1)						
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 25 \text{ V}, I_{D} = 48 \text{ A}$				200	mJ
I _{AR}	Maximum Drain-Source Avalanche Cur	rent			48	Α	
OFF CHA	RACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$					V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$				250	μΑ
			T _J = 125°C			1	mA
I _{GSSF}	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	V _{GS} = -20 V, V _{DS} = 0 V				-100	nA
ON CHAR	RACTERISTICS (Note 1)						
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2	2.9	4	V
			T _J = 125°C	1.4	2.3	3.6	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 24 \text{ A}$	•		0.02	0.025	Ω
				0.032	0.04		
I _{D(on)}	On-State Drain Current	$V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$		48			Α
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 24 \text{ A}$		10	19		S
DYNAMIC	CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, \ V_{GS} = 0 \text{ V},$			1190	1800	pF
C _{oss}	Output Capacitance	f = 1.0 MHz			475	800	pF
C _{rss}	Reverse Transfer Capacitance				150	400	pF
SWITCHII	NG CHARACTERISTICS (Note 1)					•	
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, I_{D} = 48 \text{ A},$		10	20	nS	
ţ	Tum - On Rise Time	V_{GS} = 10 V, R_{GEN} = 7.5 Ω		145	300	nS	
t _{D(off)}	Turn - Off Delay Time	1			28	60	nS
t _f	Turn - Off Fall Time				77	150	nS
Q_g	Total Gate Charge	$V_{DS} = 48 \text{ V},$			39	70	nC
$\overline{Q_{gs}}$	Gate-Source Charge	$V_{DS} = 48 \text{ V},$ $I_{D} = 48 \text{ A}, V_{GS} = 10 \text{ V}$			7.6		nC
Q _{gd}	Gate-Drain Charge				22		nC

Symbol	Parameter	Conditions	Conditions				Units
DRAIN-S	OURCE DIODE CHARACTERISTICS	•					
l _s	Maximum Continuos Drain-Source Diode			48	Α		
I _{SM}	Maximum Pulsed Drain-Source Diode Fo			144	Α		
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 24 \text{ A (Note 1)}$		0.9	1.3	V	
			T _J = 125°C		8.0	1.2	•
t _{rr}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_F = 48 \text{ A},$		35	87	140	ns
I _{rr}	Reverse Recovery Current	$dl_{F}/dt = 100 \text{ A/}\mu\text{s}$		2	3.6	8	Α
THERMA	L CHARACTERISTICS	<u>.</u>				•	
R _{øJC}	Thermal Resistance, Junction-to-Case			1.5	°C/W		
R _{eJA}	Thermal Resistance, Junction-to-Ambier			62.5	°C/W		

Note: 1. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

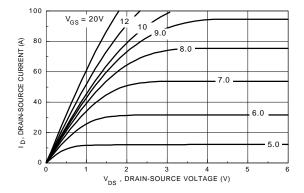


Figure 1. On-Region Characteristics

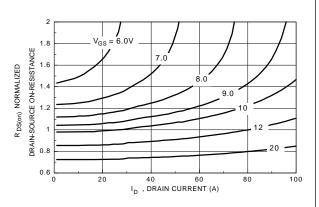


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

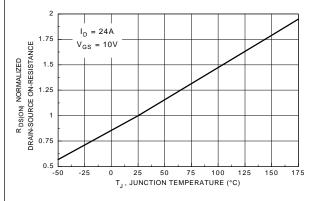


Figure 3. On-Resistance Variation with Temperature

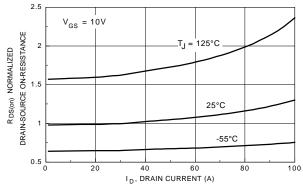


Figure 4. On-Resistance Variation with Drain Current and Temperature

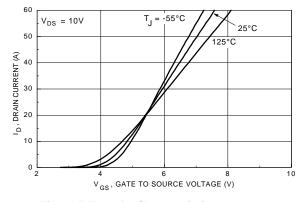


Figure 5. Transfer Characteristics

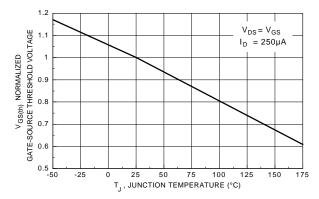


Figure 6. Gate Threshold Variation with Temperature

Typical Electrical Characteristics (continued)

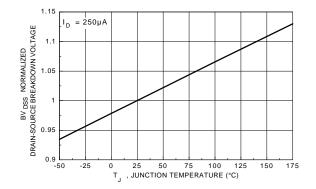


Figure 7. Breakdown Voltage Variation with Temperature

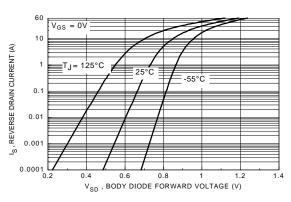


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature

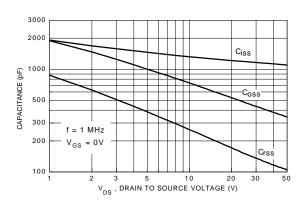


Figure 9. Capacitance Characteristics

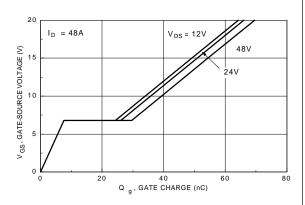


Figure 10. Gate Charge Characteristics

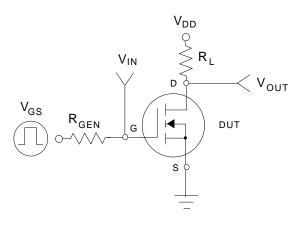


Figure 11. Switching Test Circuit

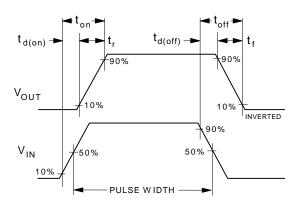
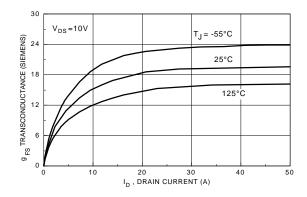


Figure 12. Switching Waveforms

Typical Electrical Characteristics (continued)



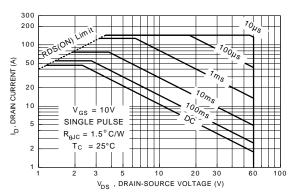


Figure 13. Transconductance Variation with Drain Current and Temperature

Figure 14. Maximum Safe Operating Area

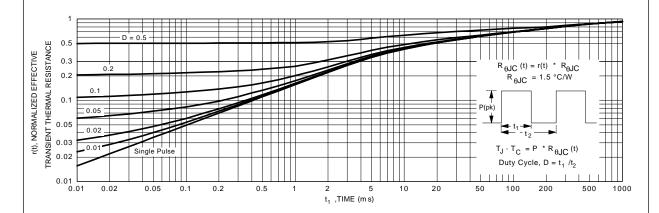
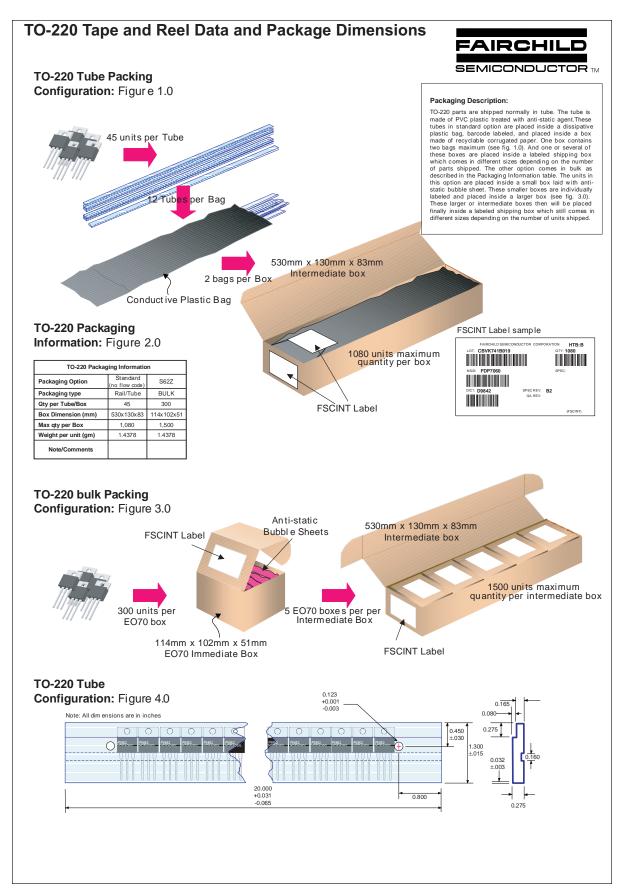
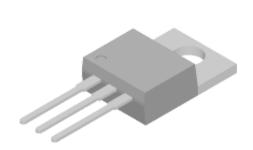


Figure 15. Transient Thermal Response Curve

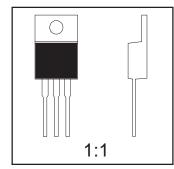


TO-220 Tape and Reel Data and Package Dimensions, continued

TO-220 (FS PKG Code 37)

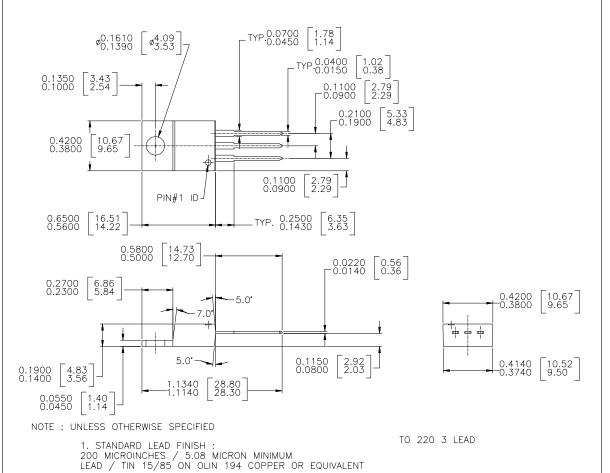


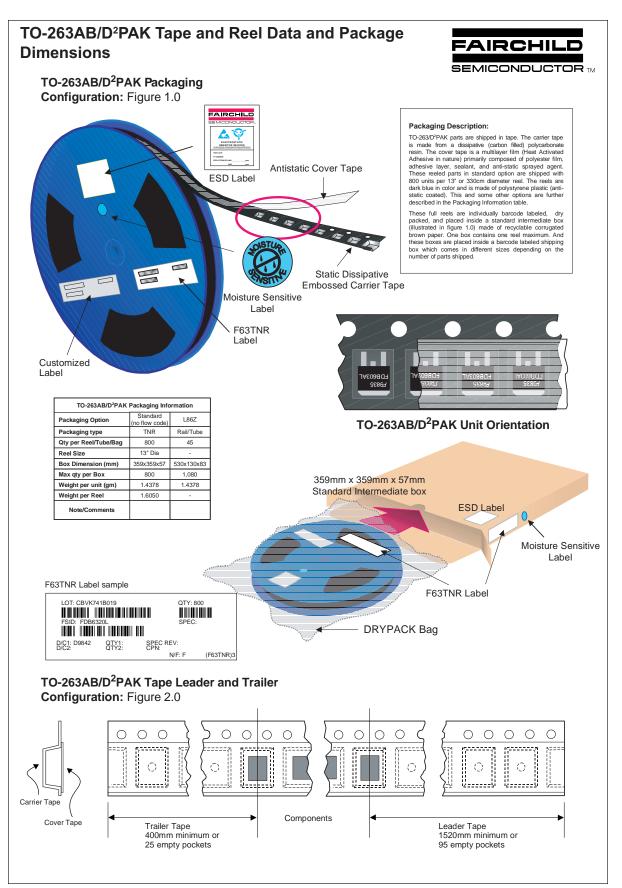
2. DIMENSION BASED ON JEDEC STANDARD TO-220 VARIATION AB, ISSUE J, DATED 3/24/87



Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

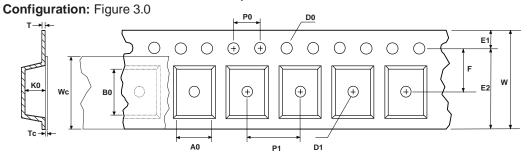
Part Weight per unit (gram): 1.4378





TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

TO-263AB/D²PAK Embossed Carrier Tape



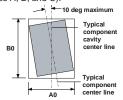
User Direction of Feed

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
TO263AB/ D²PAK (24mm)	10.60 +/-0.10	15.80 +/-0.10	24.0 +/-0.3	1.55 +/-0.05	1.60 +/-0.10	1.75 +/-0.10	22.25 min	11.50 +/-0.10	16.0 +/-0.1	4.0 +/-0.1	4.90 +/-0.10	0.450 +/-0.150	21.0 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

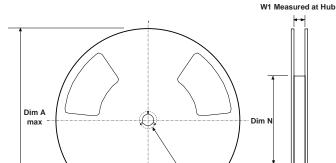


Sketch B (Top View)
Component Rotation

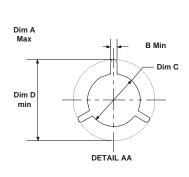


Sketch C (Top View)
Component lateral movement

TO-263AB/D²PAK Reel Configuration: Figure 4.0







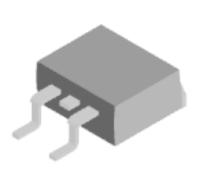
W2 max Measured at Hub

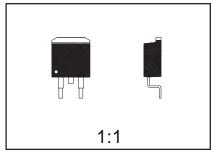
See detail AA

Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
24mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.961 +0.078/-0.000 24.4 +2/0	1.197 30.4	0.941 - 0.1.079 23.9 - 27.4

TO-263AB/D²PAK Tape and Reel Data and Package Dimensions, continued

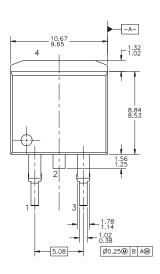
TO-263AB/D²PAK (FS PKG Code 45)

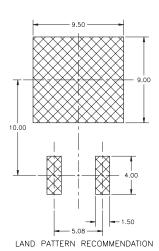


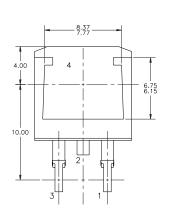


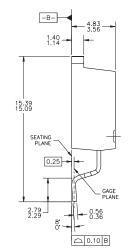
Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 1.4378









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 LEAD/TIN 15/85 ON OLIN 194 COPPER OR
 EQUIVALENT.
 C) MAXIMUM YERTICAL BURR ON HEATSINK NOT
 TO EXCEED 0.003 INCH / 0.05mm.
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